

16Mb Async. FAST SRAM Specification

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**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

16M Async FAST SRAM

Document Title

1Mx16 & 2Mx8 Bit Asynchronous FAST SRAM

Revision History

| Rev. No. | History | Draft Date | Remark |
|----------|--|------------|-------------|
| 0.0 | Initial Draft | Aug. 2012 | Preliminary |
| 1.0 | Final spec release | Jan. 2013 | Final |
| 1.1 | Add x8 org (3.3V) and 5.0V product | Aug. 2013 | Final |
| 1.2 | Add wide Vcc range support 1.65 ~ 3.6V | Sep. 2013 | Final |
| 1.3 | Add 48FBGA PKG information | Sep. 2013 | Final |
| 1.4 | Add 8ns and 12ns speed binning Change ordering information table format Remove the ordering information of -YC(I)15, -UC(I)15, -XC(I)15 | Nov. 2013 | Final |
| 1.5 | Decrease operating current value (Icc) 110mA => 85mA @8ns 90mA => 75mA @10ns 80mA => 70mA @12ns 70mA => 65mA @15ns | Sep. 2014 | Final |

S6R1616V1M, S6R1616C1M, S6R1616W1M S6R1608V1M, S6R1608C1M, S6R1608W1M 16M Async FAST SRAM

1Mx16 & 2Mx8 Bit Asynchronous FAST SRAM

Features

- Fast Access Time : 8, 10, 12, 15ns(Max)
- CMOS Low Power Dissipation
 - Standby (TTL) : 35mA (Max.)
 - (CMOS) : 28mA (Max.)
 - Operating : 85mA (8ns, Max.)
 - 75mA (10ns, Max.)
- Single 3.3±0.3V or 5.0±0.5V Power Supply
 - S6R16xxV1M : 3.3 ±0.3V Power Supply
 - S6R16xxC1M : 5.0 ±0.5V Power Supply
- Wide range of Power Supply
 - S6R16xxW1M : 1.65V ~ 3.6V Power Supply
- TTL Compatible Inputs and Outputs
- Fully Static Operation, No Clock or Refresh required
- Three State Outputs
- Data Byte Control(x16 Mode)
 - LB : I/O0~ I/O7, UB : I/O8~ I/O15
- Standard 48 TSOP1 and 48FBGA Package pin configurations for 1M x 16
- Standard 44 TSOP2 and 48FBGA Package pin configurations for 2M x 8
- ROHS compliant
- Operating in Commercial and Industrial Temperature range.

General Description

The S6R1616(V/C/W)1M and S6R1608(V/C/W)1M is a 16,789,216-bit high-speed Static Random Access Memory organized as 1M(2M) words by 16(8) bits. The S6R1616(V/C/W)1M (S6R1608(V/C/W)1M) uses 16(8) common input and output lines and have an output enable pin which operates faster than address access time at read cycle. And S6R1616(V/C/W)1M allows that lower and upper byte access by data byte control(\overline{UB} , \overline{LB}). The device is fabricated using advanced CMOS process, 6-TR based cell technology and designed for high-speed circuit technology. It is particularly well suited for use in high-density high-speed system applications.

The S6R1616(V/C/W)1M is packaged in industry standard 48 TSOP1 and 48FBGA.

The S6R1608(V/C/W)1M is packaged in industrial standard 44TSOP2 and 48FBGA.

16Mb Asynchronous FAST SRAM Ordering Information (1Mx16)

| Density | Org. | Part Number | Vcc (V) | Speed | | Package | TEMP |
|---------|-------|--------------------|---------|---------|---------|----------|--|
| | | | | tAA(ns) | tOE(ns) | | |
| 16Mb | 1Mx16 | S6R1616V1M-YC(I)08 | 3.3 | 8 | 4 | 48 TSOP1 | C : Commercial Temperature I : Industrial Temperature |
| | | S6R1616W1M-YC(I)08 | 3.3 | 8 | 4 | 48 TSOP1 | |
| | | S6R1616W1M-YC(I)08 | 2.5 | 10 | 5 | 48 TSOP1 | |
| | | S6R1616W1M-YC(I)08 | 1.8 | 12 | 6 | 48 TSOP1 | |
| | | S6R1616V1M-XC(I)08 | 3.3 | 8 | 4 | 48 FBGA | |
| | | S6R1616W1M-XC(I)08 | 3.3 | 8 | 4 | 48 FBGA | |
| | | S6R1616W1M-XC(I)08 | 2.5 | 10 | 5 | 48 FBGA | |
| | | S6R1616W1M-XC(I)08 | 1.8 | 12 | 6 | 48 FBGA | |
| | | S6R1616C1M-YC(I)10 | 5.0 | 10 | 5 | 48 TSOP1 | |
| | | S6R1616V1M-YC(I)10 | 3.3 | 10 | 5 | 48 TSOP1 | |
| | | S6R1616W1M-YC(I)10 | 3.3 | 10 | 5 | 48 TSOP1 | |
| | | S6R1616W1M-YC(I)10 | 2.5 | 10 | 5 | 48 TSOP1 | |
| | | S6R1616W1M-YC(I)10 | 1.8 | 15 | 7 | 48 TSOP1 | |
| | | S6R1616C1M-XC(I)10 | 5.0 | 10 | 5 | 48 FBGA | |
| | | S6R1616V1M-XC(I)10 | 3.3 | 10 | 5 | 48 FBGA | |
| | | S6R1616W1M-XC(I)10 | 3.3 | 10 | 5 | 48 FBGA | |
| | | S6R1616W1M-XC(I)10 | 2.5 | 10 | 5 | 48 FBGA | |
| | | S6R1616W1M-XC(I)10 | 1.8 | 15 | 7 | 48 FBGA | |

**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M 16M Async FAST SRAM**

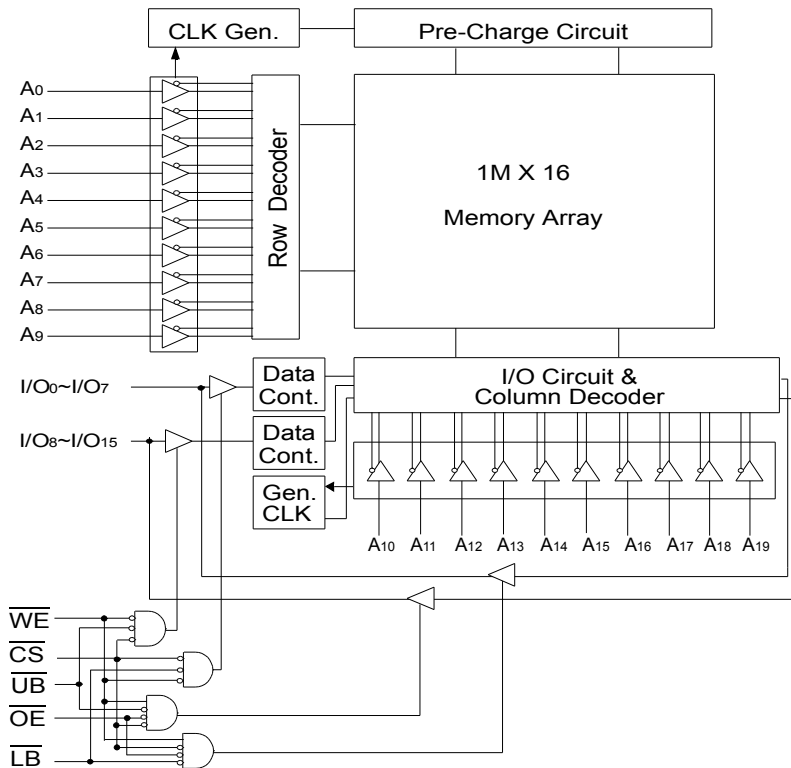
16Mb Asynchronous FAST SRAM Ordering Information (2Mx8)

| Density | Org. | Part Number | Vcc (V) | Speed | | Package | TEMP |
|---------|------|--------------------|---------|---------|---------|----------|--|
| | | | | tAA(ns) | tOE(ns) | | |
| 16Mb | 2Mx8 | S6R1608V1M-UC(I)08 | 3.3 | 8 | 4 | 44 TSOP2 | C : Commercial Temperature I : Industrial Temperature |
| | | S6R1608W1M-UC(I)08 | 3.3 | 8 | 4 | 44 TSOP2 | |
| | | S6R1608W1M-UC(I)08 | 2.5 | 10 | 5 | 44 TSOP2 | |
| | | S6R1608W1M-UC(I)08 | 1.8 | 12 | 6 | 44 TSOP2 | |
| | | S6R1608V1M-XC(I)08 | 3.3 | 8 | 4 | 48 FBGA | |
| | | S6R1608W1M-XC(I)08 | 3.3 | 8 | 4 | 48 FBGA | |
| | | S6R1608W1M-XC(I)08 | 2.5 | 10 | 5 | 48 FBGA | |
| | | S6R1608W1M-XC(I)08 | 1.8 | 12 | 6 | 48 FBGA | |
| | | S6R1608C1M-UC(I)10 | 5.0 | 10 | 5 | 44 TSOP2 | |
| | | S6R1608V1M-UC(I)10 | 3.3 | 10 | 5 | 44 TSOP2 | |
| | | S6R1608W1M-UC(I)10 | 3.3 | 10 | 5 | 44 TSOP2 | |
| | | S6R1608W1M-UC(I)10 | 2.5 | 10 | 5 | 44 TSOP2 | |
| | | S6R1608W1M-UC(I)10 | 1.8 | 15 | 7 | 44 TSOP2 | |
| | | S6R1608C1M-XC(I)10 | 5.0 | 10 | 5 | 48 FBGA | |
| | | S6R1608V1M-XC(I)10 | 3.3 | 10 | 5 | 48 FBGA | |
| | | S6R1608W1M-XC(I)10 | 3.3 | 10 | 5 | 48 FBGA | |
| | | S6R1608W1M-XC(I)10 | 2.5 | 10 | 5 | 48 FBGA | |
| | | S6R1608W1M-XC(I)10 | 1.8 | 15 | 7 | 48 FBGA | |

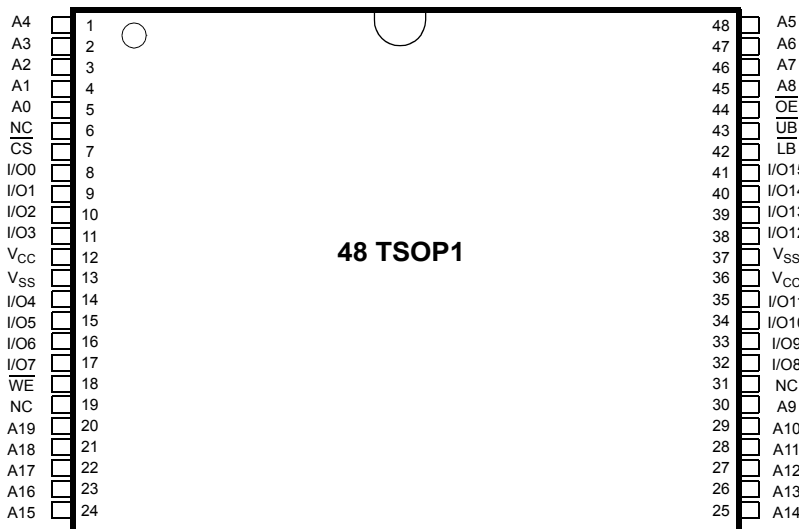
**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

16M Async FAST SRAM

Logic Block Diagram - S6R1616(V/C/W)1M (1M x 16)



48 TSOP1 Package Pin Configurations(Top View) - S6R1616(V/C/W)1M (1M x 16)



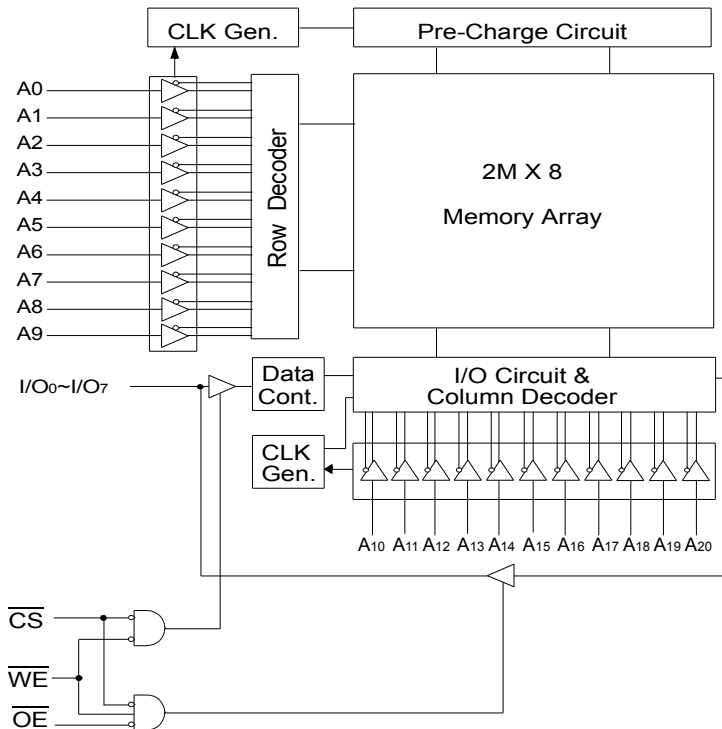
Pin Function

| Pin Name | Pin Function |
|-----------------|--------------------------------|
| A0 - A19 | Address Inputs |
| \overline{WE} | Write Enable |
| \overline{CS} | Chip Select |
| \overline{OE} | Output Enable |
| \overline{LB} | Lower-byte Control(I/O0~I/O7) |
| \overline{UB} | Upper-byte Control(I/O8~I/O15) |
| I/O0 ~ I/O15 | Data Inputs/Outputs |
| Vcc | Power |
| Vss | Ground |
| N.C | No Connection |

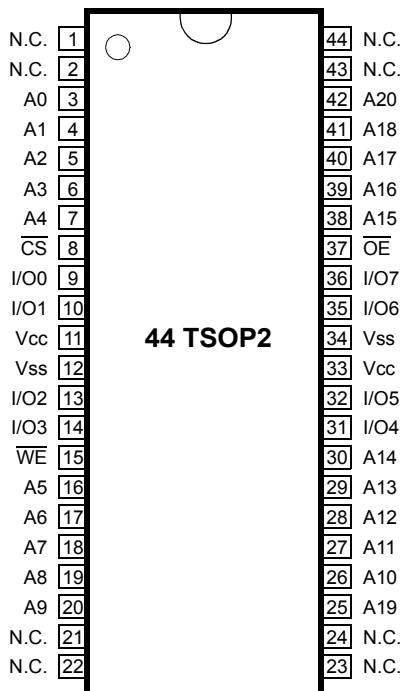
**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

16M Async FAST SRAM

Logic Block Diagram - S6R1608(V/C/W)1M (2M x 8)



44 TSOP2 Package Pin Configurations (Top View) - S6R1608(V/C/W)1M (2M x 8)



Pin Function

| Pin Name | Pin Function |
|-----------------|---------------------|
| A0 - A20 | Address Inputs |
| \overline{WE} | Write Enable |
| \overline{CS} | Chip Select |
| \overline{OE} | Output Enable |
| I/O0 ~ I/O7 | Data Inputs/Outputs |
| Vcc | Power |
| Vss | Ground |
| N.C. | No Connection |

**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M 16M Async FAST SRAM**

48FBGA - S6R1616(V/C/W)1M, 1Mx16 - Top View

PKG Pin Configurations

| | 1 | 2 | 3 | 4 | 5 | 6 |
|----------|------------------------|------------------------|-----------------|-----------------|------------------------|------------------|
| A | $\overline{\text{LB}}$ | $\overline{\text{OE}}$ | A ₀ | A ₁ | A ₂ | NC |
| B | I/O ₈ | $\overline{\text{UB}}$ | A ₃ | A ₄ | $\overline{\text{CS}}$ | I/O ₀ |
| C | I/O ₉ | I/O ₁₀ | A ₅ | A ₆ | I/O ₁ | I/O ₂ |
| D | V _{ss} | I/O ₁₁ | A ₁₇ | A ₇ | I/O ₃ | V _{cc} |
| E | V _{cc} | I/O ₁₂ | NC | A ₁₆ | I/O ₄ | V _{ss} |
| F | I/O ₁₄ | I/O ₁₃ | A ₁₄ | A ₁₅ | I/O ₅ | I/O ₆ |
| G | I/O ₁₅ | A ₁₉ | A ₁₂ | A ₁₃ | $\overline{\text{WE}}$ | I/O ₇ |
| H | A ₁₈ | A ₈ | A ₉ | A ₁₀ | A ₁₁ | NC |

Pin Function

| Pin Name | Pin Function |
|--------------------------------------|--|
| A ₀ - A ₁₉ | Address Inputs |
| $\overline{\text{WE}}$ | Write Enable |
| $\overline{\text{CS}}$ | Chip Select |
| $\overline{\text{OE}}$ | Output Enable |
| $\overline{\text{LB}}$ | Lower-byte Control(I/O ₀ ~I/O ₇) |
| $\overline{\text{UB}}$ | Upper-byte Control(I/O ₈ ~I/O ₁₅) |
| I/O ₀ ~ I/O ₁₅ | Data Inputs/Outputs |
| V _{cc} | Power |
| V _{ss} | Ground |
| NC | No Connection |

48FBGA - S6R1608(V/C/W)1M, 2Mx8 - Top View

PKG Pin Configurations

| | 1 | 2 | 3 | 4 | 5 | 6 |
|----------|-----------------|------------------------|-----------------|-----------------|------------------------|------------------|
| A | NC | $\overline{\text{OE}}$ | A ₀ | A ₁ | A ₂ | NC |
| B | NC | NC | A ₃ | A ₄ | $\overline{\text{CS}}$ | I/O ₀ |
| C | NC | NC | A ₅ | A ₆ | I/O ₁ | I/O ₂ |
| D | V _{ss} | NC | A ₁₇ | A ₇ | I/O ₃ | V _{cc} |
| E | V _{cc} | NC | NC | A ₁₆ | I/O ₄ | V _{ss} |
| F | NC | NC | A ₁₄ | A ₁₅ | I/O ₅ | I/O ₆ |
| G | NC | A ₁₉ | A ₁₂ | A ₁₃ | $\overline{\text{WE}}$ | I/O ₇ |
| H | A ₁₈ | A ₈ | A ₉ | A ₁₀ | A ₁₁ | A ₂₀ |

Pin Function

| Pin Name | Pin Function |
|-------------------------------------|---------------------|
| A ₀ - A ₂₀ | Address Inputs |
| $\overline{\text{WE}}$ | Write Enable |
| $\overline{\text{CS}}$ | Chip Select |
| $\overline{\text{OE}}$ | Output Enable |
| I/O ₀ ~ I/O ₇ | Data Inputs/Outputs |
| V _{cc} | Power |
| V _{ss} | Ground |
| NC | No Connection |

S6R1616V1M, S6R1616C1M, S6R1616W1M S6R1608V1M, S6R1608C1M, S6R1608W1M

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Absolute Maximum Ratings*

| Parameter | | Symbol | Rating | Unit |
|---|---------------------------------|------------------------------------|-------------------------------|------|
| Voltage on Any Pin Relative to VSS | 3.3V Product | V _{IN} , V _{OUT} | -0.5 to V _{CC} +0.5V | V |
| | 5.0V Product | | | |
| | Wide V _{CC} ** Product | | | |
| Voltage on V _{CC} Supply Relative to VSS | 3.3V Product | V _{IN} , V _{OUT} | -0.5 to 4.6 | V |
| | 5.0V Product | | -0.5 to 7.0 | |
| | Wide V _{CC} ** Product | | -0.5 to 4.6 | |
| Power Dissipation | | P _D | 1.0 | W |
| Storage Temperature | | T _{STG} | -65 to 150 | °C |
| Operating Temperature | Commercial | T _A | 0 to 70 | °C |
| | Industrial | T _A | -40 to 85 | °C |

* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

** Wide V_{CC} Range is 1.65V ~ 3.6V

Recommended DC Operating Conditions* (T_A=0 to 70°C)

| Parameter | Operating V _{CC} (V) | Symbol | Min | Typ | Max | Unit |
|--------------------|-------------------------------|-----------------|------|---------|----------------------|------|
| Supply Voltage | 5.0 | V _{CC} | 4.5 | 5.0 | 5.5 | V |
| | 3.3 | V _{CC} | 3.0 | 3.3 | 3.6 | |
| | Wide 2.4 ~ 3.6 | V _{CC} | 2.4 | 2.5/3.3 | 3.6 | |
| | Wide 1.65 ~ 2.2 | V _{CC} | 1.65 | 1.8 | 2.2 | |
| Ground | | V _{SS} | 0 | 0 | 0 | V |
| Input High Voltage | 5.0 | V _{IH} | 2.2 | - | V _{CC} +0.5 | V |
| | 3.3 | V _{IH} | 2.0 | - | V _{CC} +0.5 | |
| | Wide 2.4 ~ 3.6 | V _{IH} | 2.0 | - | V _{CC} +0.3 | |
| | Wide 1.65 ~ 2.2 | V _{IH} | 1.4 | - | V _{CC} +0.2 | |
| Input Low Voltage | 5.0 | V _{IL} | -0.3 | - | 0.8 | V |
| | 3.3 | V _{IL} | -0.3 | - | 0.8 | |
| | Wide 2.4 ~ 3.6 | V _{IL} | -0.3 | - | 0.7 | |
| | Wide 1.65 ~ 2.2 | V _{IL} | -0.2 | - | 0.4 | |

* The above parameters are also guaranteed for industrial temperature range.

S6R1616V1M, S6R1616C1M, S6R1616W1M S6R1608V1M, S6R1608C1M, S6R1608W1M

16M Async FAST SRAM

DC and Operating Characteristics* (TA=0 to 70°C)

| Parameter | Symbol | Test Conditions | Min | Max | Unit | |
|---------------------------|------------------|--|------|-----|------|----|
| Input Leakage Current | I _{LI} | V _{IN} =V _{SS} to V _{CC} | -2 | 2 | μA | |
| Output Leakage Current | I _{LO} | $\overline{CS}=V_{IH}$ or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$ V _{OUT} =V _{SS} to V _{CC} | -2 | 2 | μA | |
| Operating Current** | I _{CC} | Min. Cycle, 100% Duty CS=V _{IL} , V _{IN} =V _{IH} or V _{IL} , I _{OUT} =0mA | 8ns | - | 85 | mA |
| | | | 10ns | - | 75 | |
| | | | 12ns | - | 70 | |
| | | | 15ns | - | 65 | |
| Standby Current | I _{SB} | Min. Cycle, $\overline{CS}=V_{IH}$ | - | 35 | mA | |
| | I _{SB1} | f=0MHz, $\overline{CS} \geq V_{CC}-0.2V$, V _{IN} ≥ V _{CC} -0.2V or V _{IN} ≤ 0.2V | - | 28 | | |
| Output Low Voltage Level | V _{OL} | V _{CC} =4.5V, I _{OL} =8mA, 5.0V Product | - | 0.4 | V | |
| | | V _{CC} =3.0V, I _{OL} =8mA, 3.3V & Wide V _{CC} ** Product | - | 0.4 | | |
| | | V _{CC} =2.4V, I _{OL} =1mA, Wide V _{CC} ** Product | - | 0.4 | | |
| | | V _{CC} =1.65V, I _{OL} =0.1mA, Wide V _{CC} ** Product | - | 0.2 | | |
| Output High Voltage Level | V _{OH} | V _{CC} =4.5V, I _{OH} =-4mA, 5.0V Product | 2.4 | - | V | |
| | | V _{CC} =3.0V, I _{OH} =-4mA, 3.3V & Wide V _{CC} ** Product | 2.4 | - | | |
| | | V _{CC} =2.4V, I _{OH} =-1mA, Wide V _{CC} ** Product | 1.8 | - | | |
| | | V _{CC} =1.65V, I _{OH} =-0.1mA, Wide V _{CC} ** Product | 1.4 | - | | |

* The above parameters are also guaranteed for industrial temperature range.

** Wide V_{CC} Range is 1.65V ~ 3.6V

Capacitance* (TA=25°C, f=1.0MHz)

| Item | Symbol | Test Conditions | TYP | Max | Unit |
|--------------------------|------------------|----------------------|-----|-----|------|
| Input/Output Capacitance | C _{I/O} | V _{I/O} =0V | - | 8 | pF |
| Input Capacitance | C _{IN} | V _{IN} =0V | - | 6 | pF |

* Capacitance is sampled and not 100% tested.

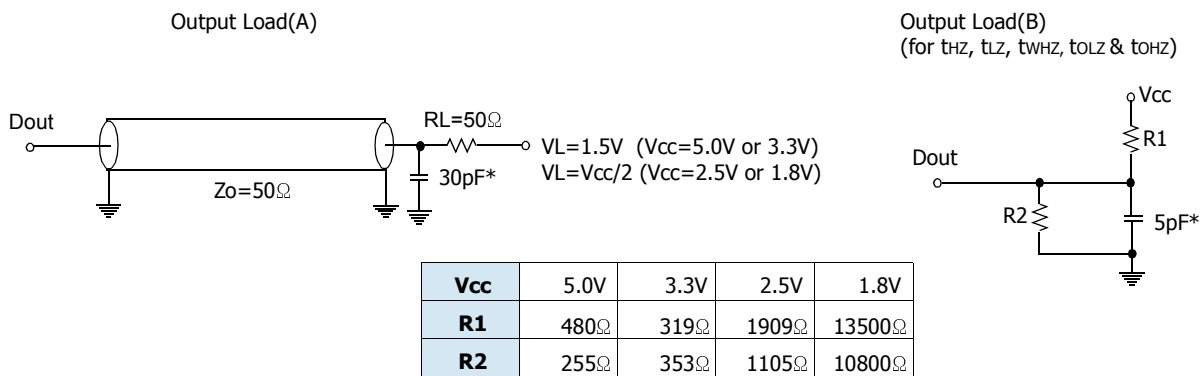
S6R1616V1M, S6R1616C1M, S6R1616W1M S6R1608V1M, S6R1608C1M, S6R1608W1M

16M Async FAST SRAM

Test Conditions*

| Parameter | Value |
|--|------------------------------|
| Input Pulse Level | 0 to 3.0V (Vcc=3.3V or 5.0V) |
| | 0 to 2.5V (Vcc=2.5V) |
| | 0 to 1.8V (Vcc=1.8V) |
| Input Rise and Fall Time | 1V/1ns |
| Input and Output Timing Reference Levels | 1.5V (Vcc=3.3V or 5.0V) |
| | 1/2Vcc (Vcc= 1.8V or 2.5V) |
| Output Load | See Fig. 1 |

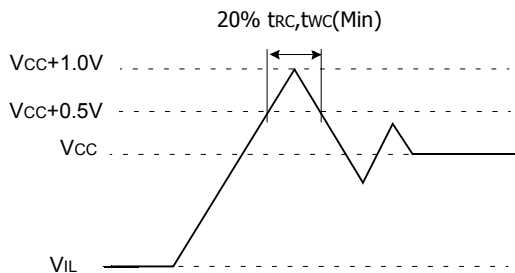
* The above parameters are also guaranteed at industrial temperature range.



* Including Scope and Jig Capacitance

Fig. 1

Overshoot Timing



Undershoot Timing

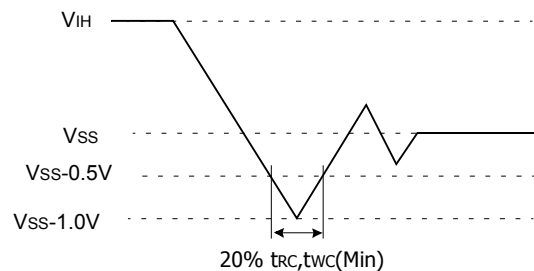


Fig. 2

Functional Description (x8 Mode)

| $\overline{\text{CS}}$ | $\overline{\text{WE}}$ | $\overline{\text{OE}}$ | Mode | I/O Pin | Supply Current |
|------------------------|------------------------|------------------------|----------------|---------|----------------|
| H | X | X* | Not Select | High-Z | ISB, ISB1 |
| L | H | H | Output Disable | High-Z | Icc |
| L | H | L | Read | DOUT | Icc |
| L | L | X | Write | DIN | Icc |

* X means Don't Care.

S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M

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Functional Description (x16 Mode)

| \overline{CS} | \overline{WE} | \overline{OE} | \overline{LB}^{**} | \overline{UB}^{**} | Mode | I/O Pin | | Supply Current |
|-----------------|-----------------|-----------------|----------------------|----------------------|----------------|------------------------------------|-------------------------------------|------------------------------------|
| | | | | | | I/O ₀ ~I/O ₇ | I/O ₈ ~I/O ₁₅ | |
| H | X | X* | X | X | Not Select | High-Z | High-Z | I _{SB} , I _{SB1} |
| L | H | H | X | X | Output Disable | High-Z | High-Z | I _{CC} |
| L | X | X | H | H | | | | |
| L | H | L | L | H | Read | DOUT | High-Z | I _{CC} |
| | | | H | L | | High-Z | DOUT | |
| | | | L | L | | DOUT | DOUT | |
| L | L | X | L | H | Write | DIN | High-Z | I _{CC} |
| | | | H | L | | High-Z | DIN | |
| | | | L | L | | DIN | DIN | |

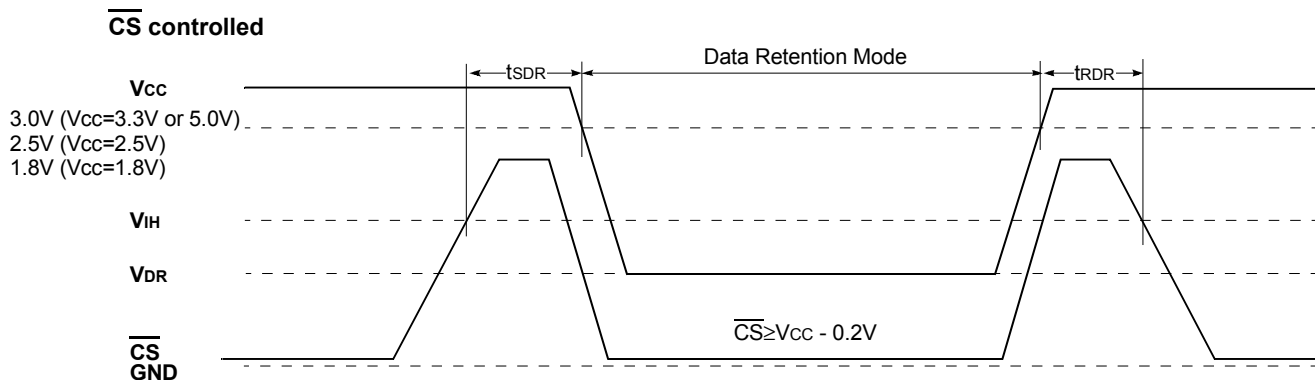
* X means Don't Care.

Data Retention Characteristics* (T_A=0 to 70°C)

| Parameter | Product | Operating V _{CC} (V) | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|------------------------------------|-------------------|-------------------------------|------------------|---|------|------|------|------|
| V _{CC} for Data Retention | 5.0V Product | 5.0 | V _{DR} | $\overline{CS} \geq V_{CC} - 0.2V$ | 2.0 | - | 5.5 | V |
| | 3.3V Product | 3.3 | | | 2.0 | - | 3.6 | |
| | Wide 2.4V ~ 3.6V | 2.5/3.3 | | | 2.0 | - | 3.6 | |
| | Wide 1.65V ~ 2.2V | 1.8 | | | 1.5 | - | 3.6 | |
| Data Retention Current | 5.0V Product | 5.0 | I _{DR} | V _{CC} =2.0V $\overline{CS} \geq V_{CC} - 0.2V$ V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V | - | - | 20 | mA |
| | 3.3V Product | 3.3 | | | - | - | 20 | |
| | Wide 2.4V ~ 3.6V | 2.5/3.3 | | | - | - | 28 | |
| | Wide 1.65V ~ 2.2V | 1.8 | | V _{CC} =1.5V $\overline{CS} \geq V_{CC} - 0.2V$ V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V | - | - | 28 | |
| Data Retention Set-Up Time | | | t _{SDR} | See Data Retention Wave form(below) | 0 | - | - | ns |
| Recovery Time | | | t _{RDR} | | 5 | - | - | ms |

* The above parameters are also guaranteed at industrial temperature range.

Data Retention Wave Form



S6R1616V1M, S6R1616C1M, S6R1616W1M S6R1608V1M, S6R1608C1M, S6R1608W1M

16M Async FAST SRAM

Read Cycle*

| Parameter | Symbol | 8ns | | 10ns | | 12ns | | 15ns | | Unit |
|---|------------------|-----|-----|------|-----|------|-----|------|-----|------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | |
| Read Cycle Time | t _{RC} | 8 | - | 10 | - | 12 | - | 15 | - | ns |
| Address Access Time | t _{AA} | - | 8 | - | 10 | - | 12 | - | 15 | ns |
| Chip Select to Output | t _{CO} | - | 8 | - | 10 | - | 12 | - | 15 | ns |
| Output Enable to Valid Output | t _{OE} | - | 4 | - | 5 | - | 6 | - | 7 | ns |
| \overline{UB} , \overline{LB} Access Time ** | t _{BA} | - | 4 | - | 5 | - | 6 | - | 7 | ns |
| Chip Enable to Low-Z Output | t _{LZ} | 3 | - | 3 | - | 3 | - | 3 | - | ns |
| Output Enable to Low-Z Output | t _{OLZ} | 0 | - | 0 | - | 0 | - | 0 | - | ns |
| \overline{UB} , \overline{LB} Enable to Low-Z Output ** | t _{BLZ} | 0 | - | 0 | - | 0 | - | 0 | - | ns |
| Chip Disable to High-Z Output | t _{HZ} | 0 | 4 | 0 | 5 | 0 | 6 | 0 | 7 | ns |
| Output Disable to High-Z Output | t _{OHZ} | 0 | 4 | 0 | 5 | 0 | 6 | 0 | 7 | ns |
| \overline{UB} , \overline{LB} Disable to High-Z Output ** | t _{BHZ} | 0 | 4 | 0 | 5 | 0 | 6 | 0 | 7 | ns |
| Output Hold from Address Change | t _{OH} | 3 | - | 3 | - | 3 | - | 3 | - | ns |
| Chip Selection to Power Up Time | t _{PU} | 0 | - | 0 | - | 0 | - | 0 | - | ns |
| Chip Selection to Power Down Time | t _{PD} | - | 8 | - | 10 | - | 12 | - | 15 | ns |

* The above parameters are also guaranteed for industrial temperature range.

Write Cycle*

| Parameter | Symbol | 8ns | | 10ns | | 12ns | | 15ns | | Unit |
|--|------------------|-----|-----|------|-----|------|-----|------|-----|------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | |
| Write Cycle Time | t _{WC} | 8 | - | 10 | - | 12 | - | 15 | - | ns |
| Chip Select to End of Write | t _{CW} | 6 | - | 7 | - | 9 | - | 12 | - | ns |
| Address Set-up Time | t _{AS} | 0 | - | 0 | - | 0 | - | 0 | - | ns |
| Address Valid to End of Write | t _{AW} | 6 | - | 7 | - | 9 | - | 12 | - | ns |
| Write Pulse Width(\overline{OE} High) | t _{WP} | 6 | - | 7 | - | 9 | - | 12 | - | ns |
| Write Pulse Width(\overline{OE} Low) | t _{WP1} | 8 | - | 10 | - | 12 | - | 15 | - | ns |
| \overline{UB} , \overline{LB} Valid to End of Write ** | t _{BW} | 6 | - | 7 | - | 9 | - | 12 | - | ns |
| Write Recovery Time | t _{WR} | 0 | - | 0 | - | 0 | - | 0 | - | ns |
| Write to Output High-Z | t _{WHZ} | 0 | 4 | 0 | 5 | 0 | 6 | 0 | 7 | ns |
| Data to Write Time Overlap | t _{DW} | 4 | - | 5 | - | 7 | - | 8 | - | ns |
| Data Hold from Write Time | t _{DH} | 0 | - | 0 | - | 0 | - | 0 | - | ns |
| End of Write to Output Low-Z | t _{OW} | 3 | - | 3 | - | 3 | - | 3 | - | ns |

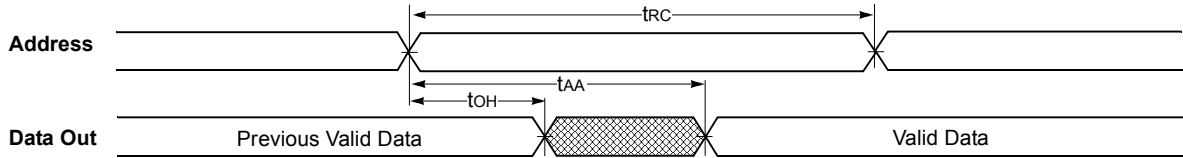
* The above parameters are also guaranteed for industrial temperature range.

**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

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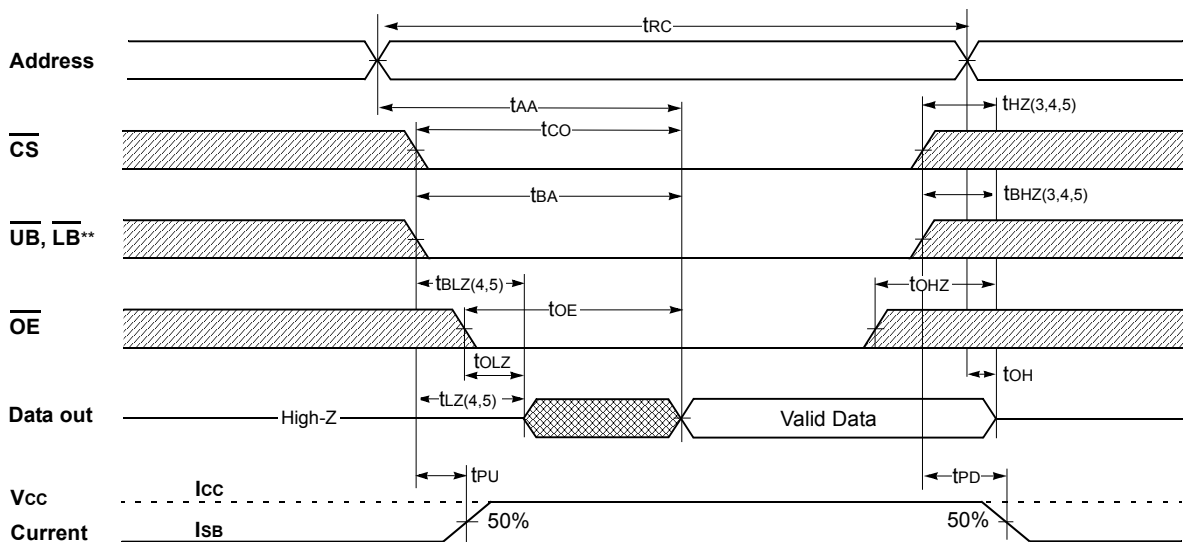
Timing Diagrams

Timing Waveform Of Read Cycle(1) (Address Controlled, $\overline{CS}=\overline{OE}=V_{IL}$, $\overline{WE}=V_{IH}$, $\overline{UB}, \overline{LB}=V_{IL}$ **)



** Those parameters are applied for x16 mode only.

Timing Waveform Of Read Cycle(2) ($\overline{WE}=V_{IH}$)

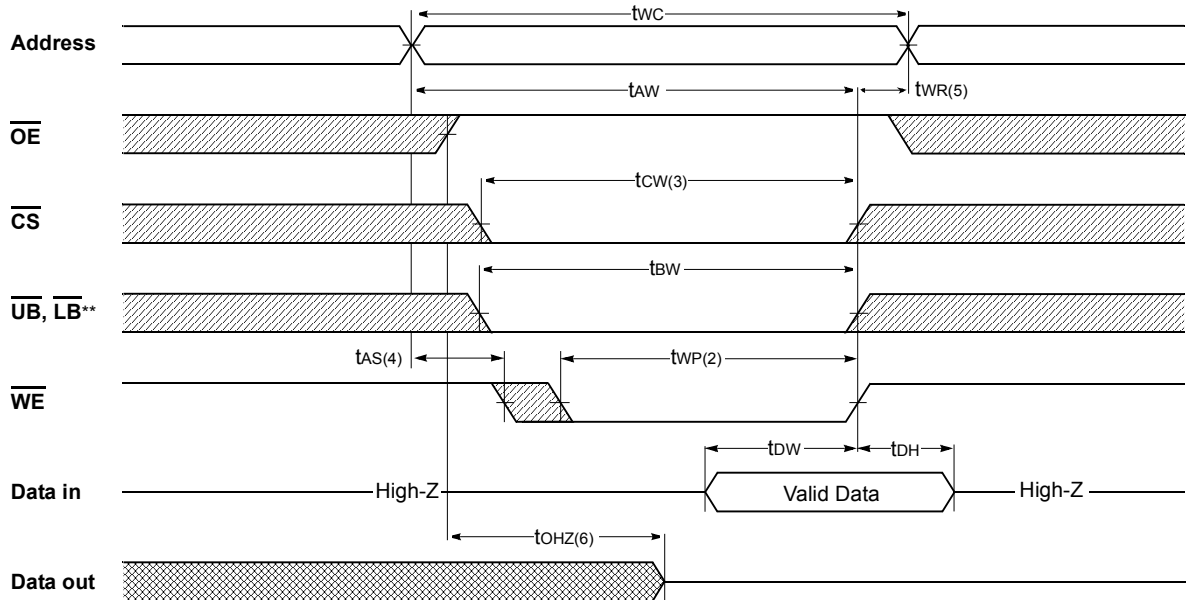


NOTES(Read Cycle)

1. \overline{WE} is high for read cycle.
2. All read cycle timing is referenced from the last valid address to the first transition address.
3. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are not referenced to V_{OH} or V_{OL} levels.
4. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device.
5. Transition is measured $\pm 200\text{mV}$ from steady state voltage with Load(B). This parameter is sampled and not 100% tested.
6. Device is continuously selected with $\overline{CS}=V_{IL}$.
7. Address valid prior to coincident with \overline{CS} transition low.
8. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.

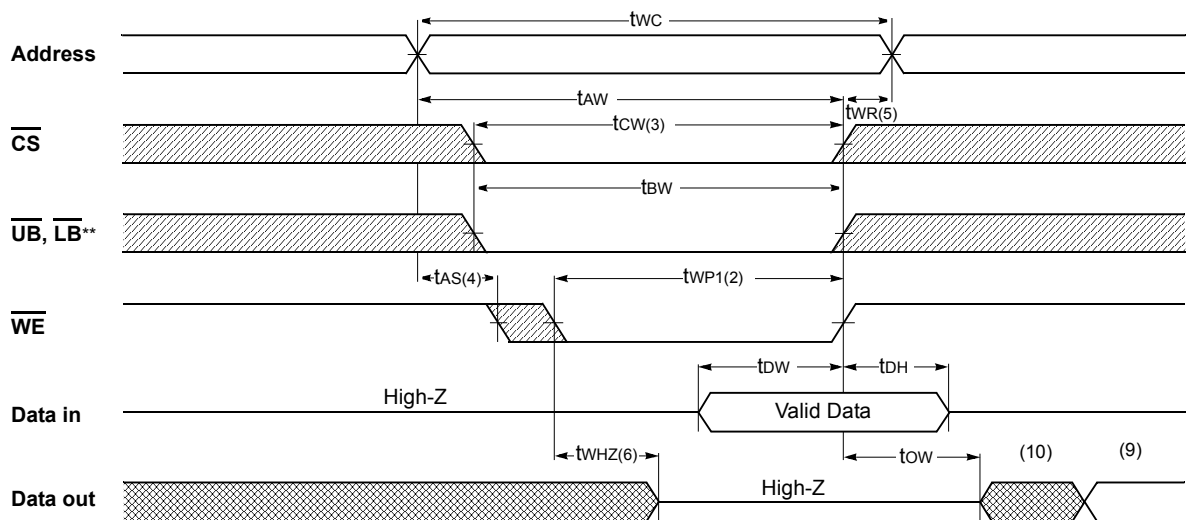
** Those parameters are applied for x16 mode only.

Timing Waveform Of Write Cycle(1) (\overline{OE} Clock)



** Those parameters are applied for x16 mode only.

Timing Waveform Of Write Cycle(2) (\overline{OE} =Low fixed)

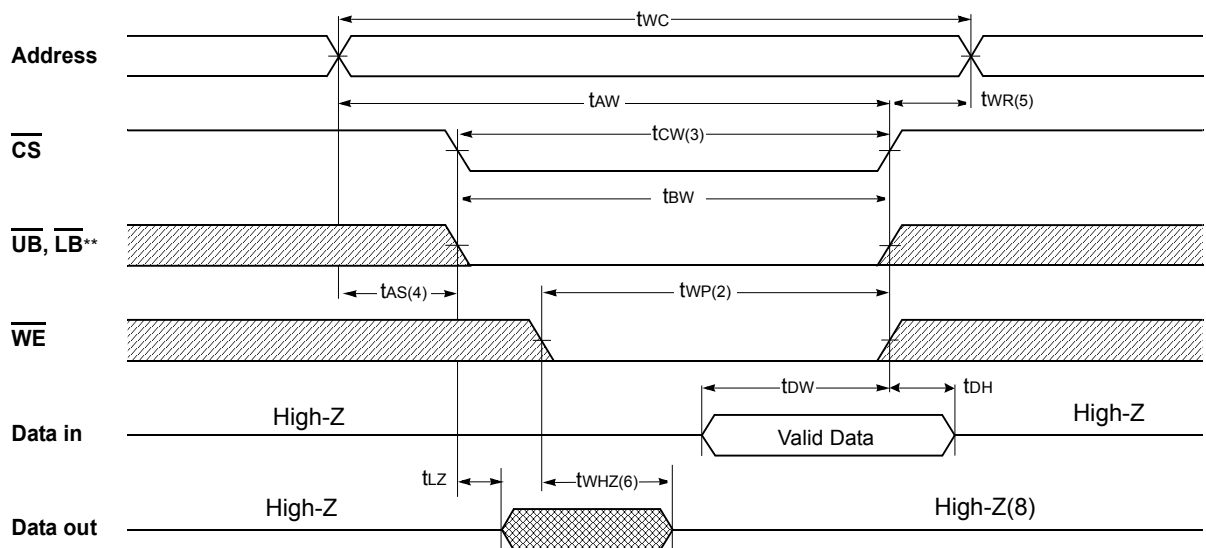


** Those parameters are applied for x16 mode only.

**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

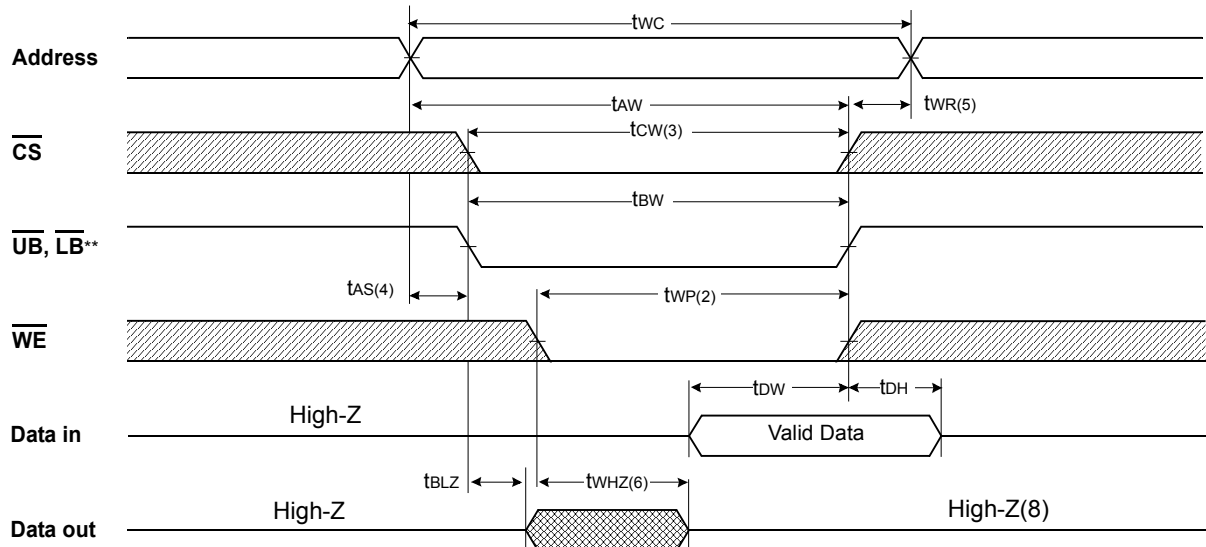
16M Async FAST SRAM

Timing Waveform Of Write Cycle(3) (\overline{CS} =Controlled)



** Those parameters are applied for x16 mode only.

Timing Waveform Of Write Cycle(4) (\overline{UB} , \overline{LB} Controlled)



NOTES(Write Cycle)

1. All write cycle timing is referenced from the last valid address to the first transition address.
2. A write occurs during the overlap of a low \overline{CS} , \overline{WE} , \overline{LB} and \overline{UB} . A write begins at the latest transition \overline{CS} going low and \overline{WE} going low ; A write ends at the earliest transition \overline{CS} going high or \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.
3. t_{CW} is measured from the later of \overline{CS} going low to end of write.
4. t_{AS} is measured from the address valid to the beginning of write.
5. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as \overline{CS} or \overline{WE} going high.
6. If \overline{OE} , \overline{CS} and \overline{WE} are in the Read Mode during this period, the I/O pins are in the output low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
7. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
8. If \overline{CS} goes low simultaneously with \overline{WE} going or after \overline{WE} going low, the outputs remain high impedance state.
9. Dout is the read data of the new address.
10. When \overline{CS} is low : I/O pins are in the output state. The input signals in the opposite phase leading to the output should not be applied.

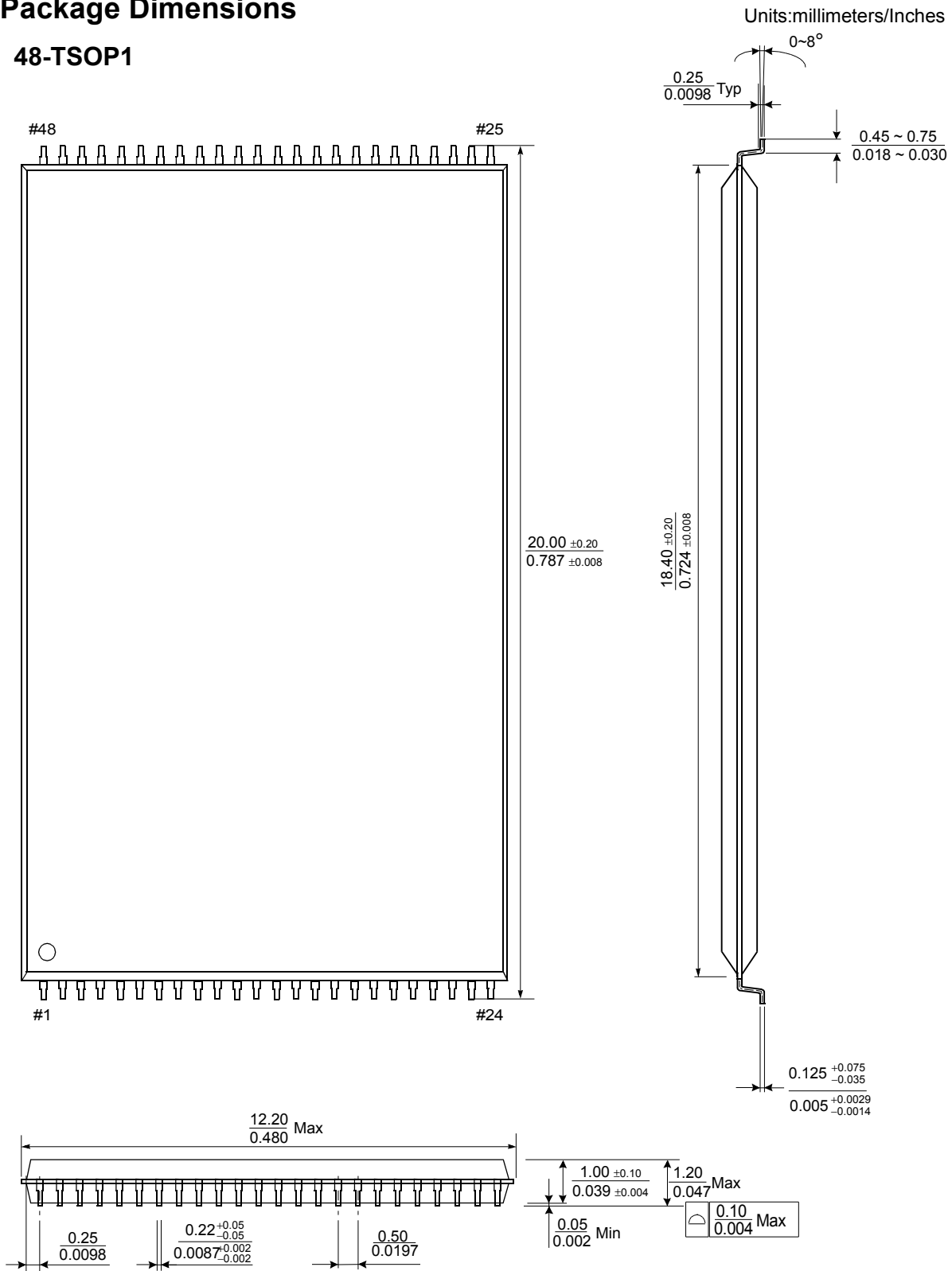
** Those parameters are applied for x16 mode only.

**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

16M Async FAST SRAM

Package Dimensions

48-TSOP1

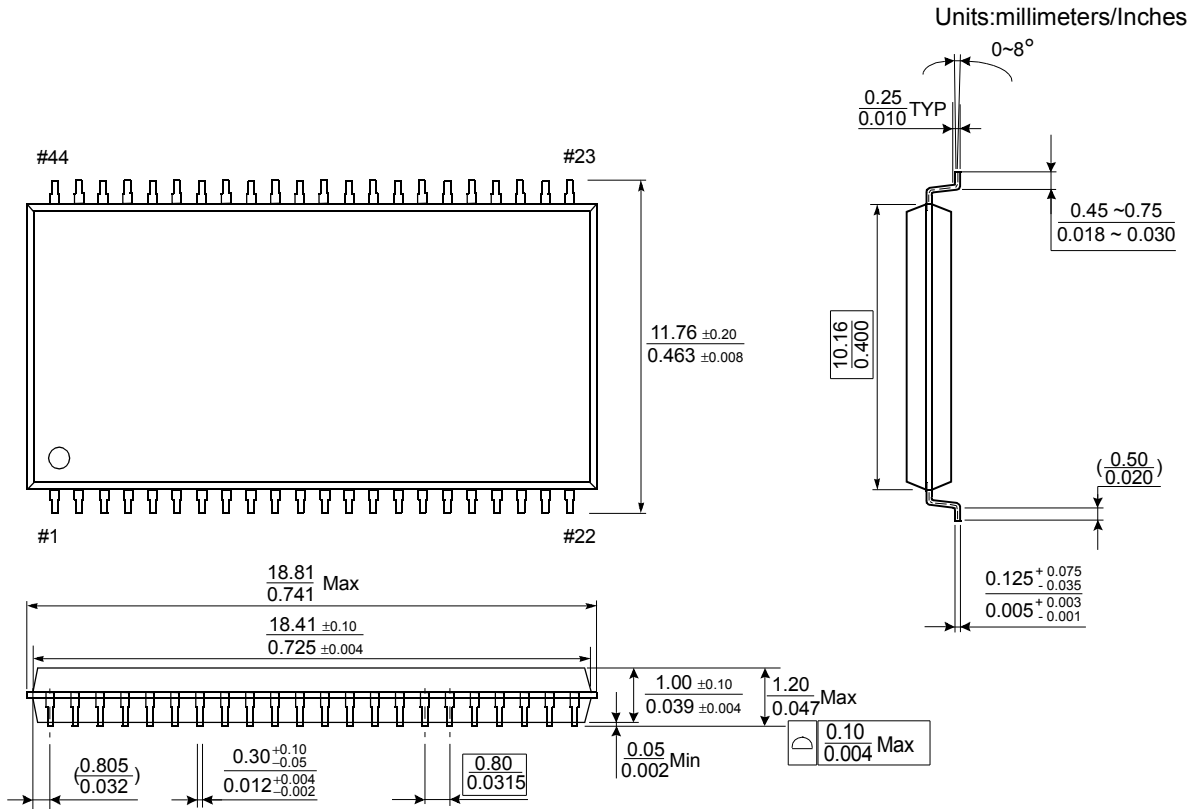


**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

16M Async FAST SRAM

Package Dimensions

44-TSOP2-400BF



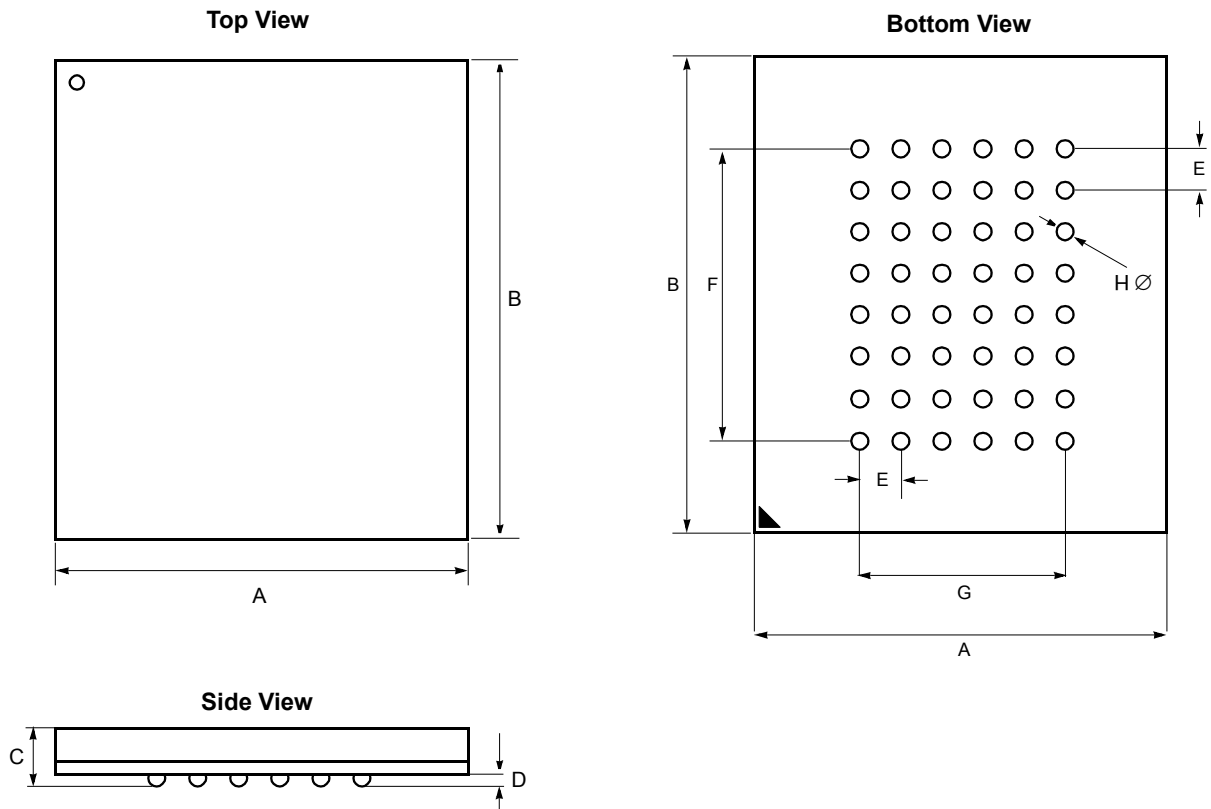
**S6R1616V1M, S6R1616C1M, S6R1616W1M
S6R1608V1M, S6R1608C1M, S6R1608W1M**

16M Async FAST SRAM

Package Dimensions

48-FBGA

6mm x 8mm Body, 0.75mm Bump Pitch, 6 x 8 Ball Grid Array



| Symbol | Value | Units | Note | Symbol | Value | Units | Note |
|----------|-------------|-------|------|----------|-------------|-------|------|
| A | 6 ± 0.1 | mm | | E | 0.75 | mm | |
| B | 8 ± 0.1 | mm | | F | 5.25 | mm | |
| C | 1.1 ± 0.1 | mm | | G | 3.75 | mm | |
| D | 0.25 ± 0.05 | mm | | H | 0.35 ± 0.05 | mm | |